THE DATASHEET OF

NTR1P02LT3G

NTR1P02L, NVTR01P02L

MOSFET – Power, P-Channel, SOT-23

-20 V, -1.3 A

These miniature surface mount MOSFETs low $R_{DS(on)}$ assure minimal power loss and conserve energy, making these devices ideal for use in space sensitive power management circuitry. Typical applications are DC−DC converters and power management in portable and battery−powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low $R_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SOT−23 Surface Mount Package Saves Board Space
- NVTR Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- Pb−Free and Halide−Free Packages are Available

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage	V_{DSS}	−20	V
Gate−to−Source Voltage − Continuous	V_{GS}	±12	V
Drain Current − Continuous @ T_A = 25°C − Pulsed Drain Current ($t_p \le 10$ μs)	I_D I_{DM}	−1.3 −4.0	A A
Total Power Dissipation @ T_A = 25°C	P_D	400	mW
Operating and Storage Temperature Range	T_J, T_{stg}	− 55 to 150	°C
Thermal Resistance − Junction−to−Ambient	$R_{\theta JA}$	300	°C/W
Maximum Lead Temperature for Soldering Purposes, (1/8″ from case for 10 s)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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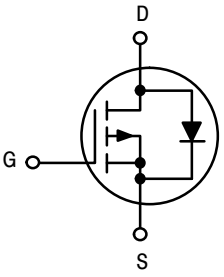
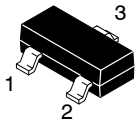
$V_{(BR)DSS}$	$R_{DS(on)}$ Max	I_D Max
−20 V	220 mΩ @ −4.5 V	−1.3 A

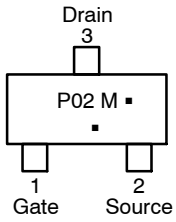
P−Channel



MARKING DIAGRAM & PIN ASSIGNMENT



SOT−23
CASE 318
STYLE 21



P02 = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTR1P02LT1G	SOT−23 (Pb−Free)	3000 Tape & Reel
NTR1P02LT3G	SOT−23 (Pb−Free)	10,000 Tape & Reel
NVTR01P02LT1G	SOT−23 (Pb−Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Parameter	Test Condition	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	(V_{GS} = 0 V, I_D = −10 μA)	$V_{(BR)DSS}$	−20			V
Zero Gate Voltage Drain Current	(V_{DS} = −16 V, V_{GS} = 0 V) (V_{DS} = −16 V, V_{GS} = 0 V, T_J = 125°C)	I_{DSS}			−1.0 −10	μA
Gate−Body Leakage Current	(V_{GS} = ± 12 V, V_{DS} = 0 V)	I_{GSS}			±100	nA
ON CHARACTERISTICS (Note 1)						
Gate Threshold Voltage	(V_{DS} = V_{GS}, I_D = −250 μA)	$V_{GS(th)}$	−0.7	−1.0	−1.25	V
Static Drain−to−Source On−Resistance	(V_{GS} = −4.5 V, I_D = −0.75 A) (V_{GS} = −2.5 V, I_D = −0.5 A)	$r_{DS(on)}$		0.140 0.200	0.22 0.35	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V_{DS} = −5.0 V)	C_{iss}		225		pF
Output Capacitance	(V_{DS} = −5.0 V)	C_{oss}		130		
Transfer Capacitance	(V_{DS} = −5.0 V)	C_{rss}		55		
SWITCHING CHARACTERISTICS (Note 2)						
Turn−On Delay Time	(V_{GS} = −4.5 V, V_{DD} = −5.0 V, I_D = −1.0 A, R_L = 5.0 Ω, R_G = 6.0 Ω)	$t_{d(on)}$		7.0		ns
Rise Time		t_r		15		
Turn−Off Delay Time		$t_{d(off)}$		18		
Fall Time		t_f		9		
Total Gate Charge	(V_{DS} = −16 V, I_D = −1.5 A, V_{GS} = −4.5 V)	Q_T		3.1		nC
SOURCE−DRAIN DIODE CHARACTERISTICS						
Continuous Current		I_S			−0.6	A
Pulsed Current		I_{SM}			−0.75	
Forward Voltage (Note 2)	(V_{GS} = 0 V, I_S = −0.6 A)	V_{SD}			−1.0	V
Reverse Recovery Time	(I_S = −1.0 A, V_{GS} = 0 V, dI_S/dt = 100 A/μs)	t_{rr}		16		ns
		t_a		11		
		t_b		5.5		
Reverse Recovery Stored Charge		Q_{RR}		8.5		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.

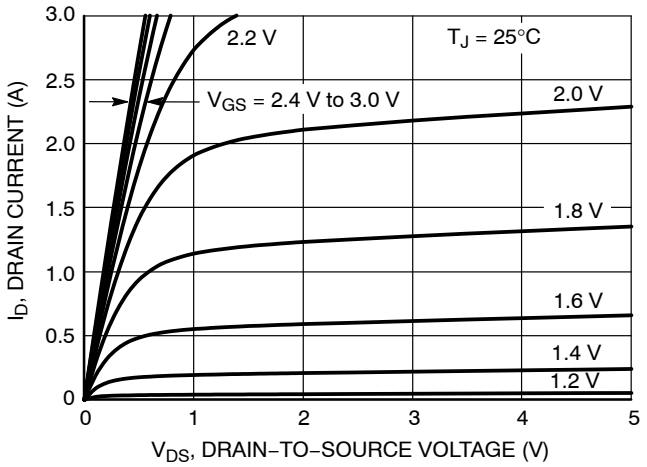


Figure 1. On−Region Characteristics

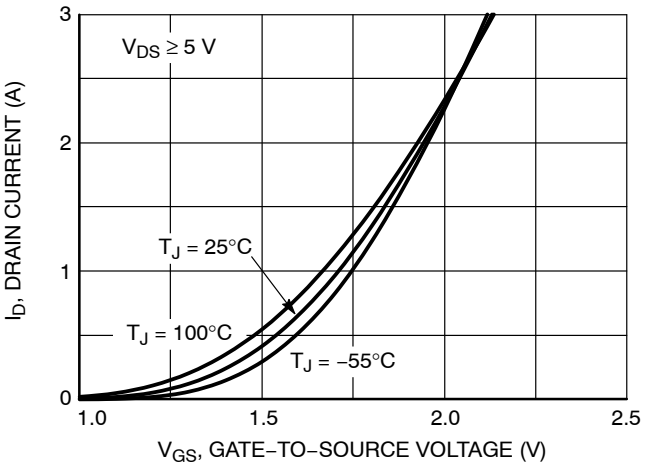


Figure 2. Transfer Characteristics

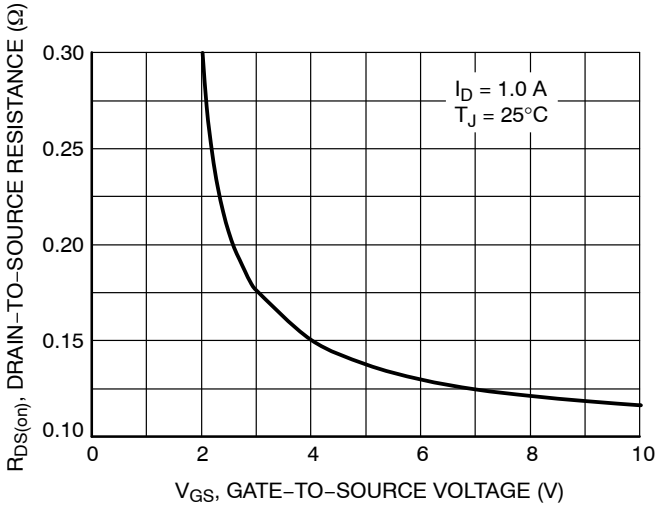


Figure 3. On−Resistance vs. Gate−to−Source Voltage

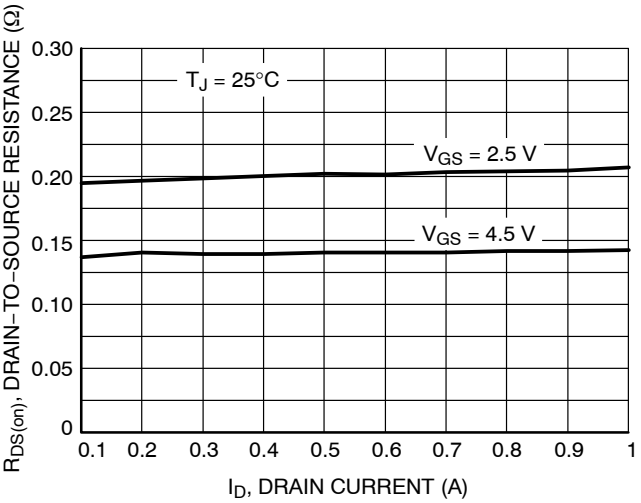


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

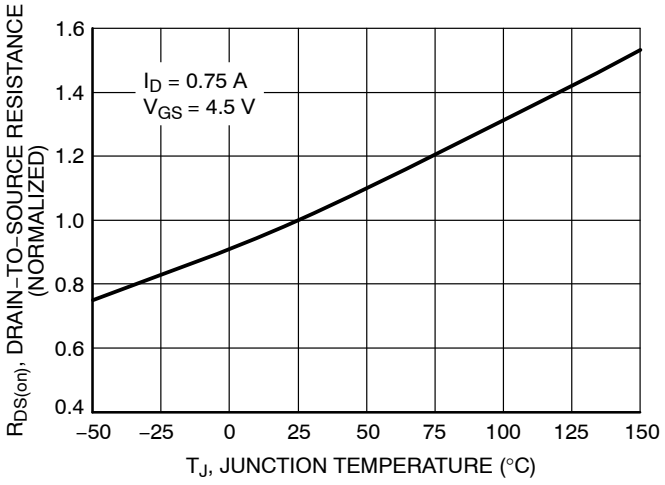


Figure 5. On−Resistance Variation with Temperature

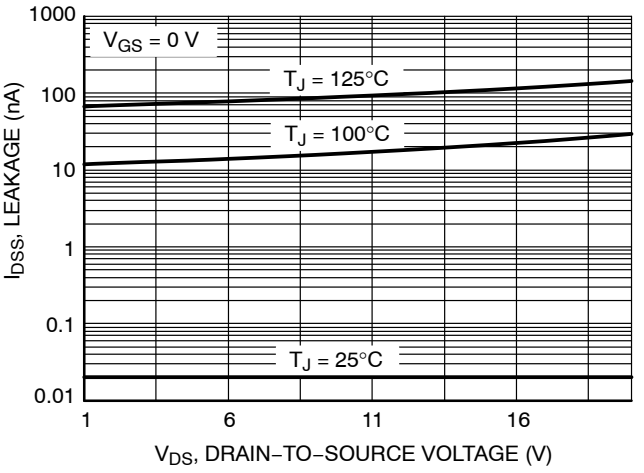


Figure 6. Drain−to−Source Leakage Current vs. Voltage

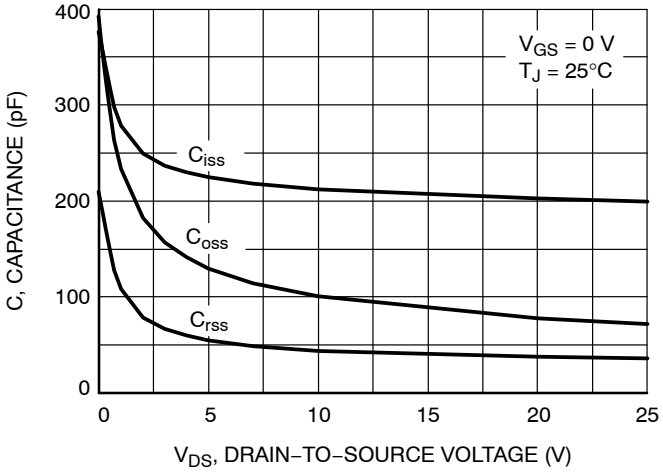


Figure 7. Capacitance Variation

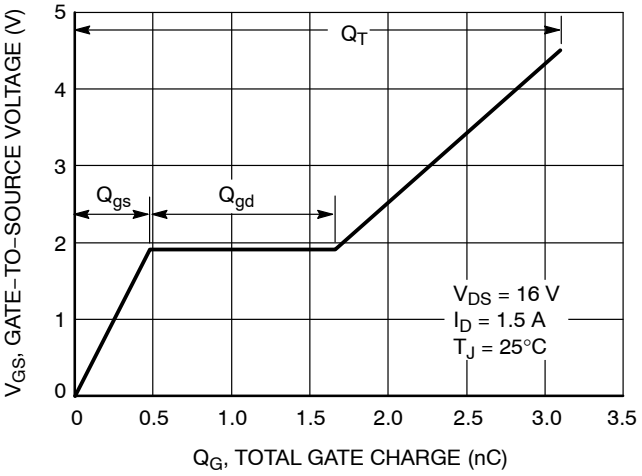


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

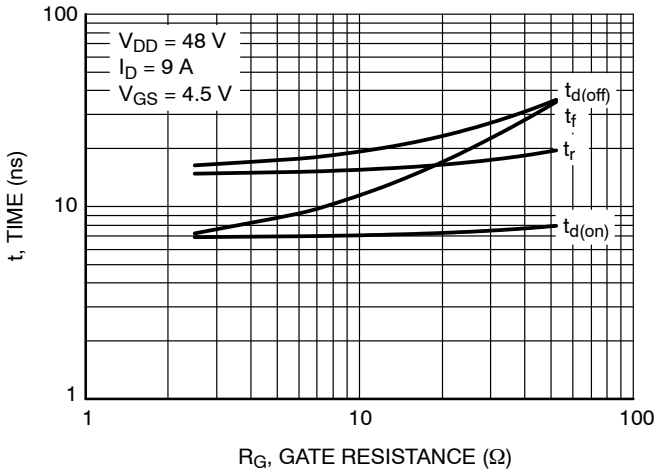


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

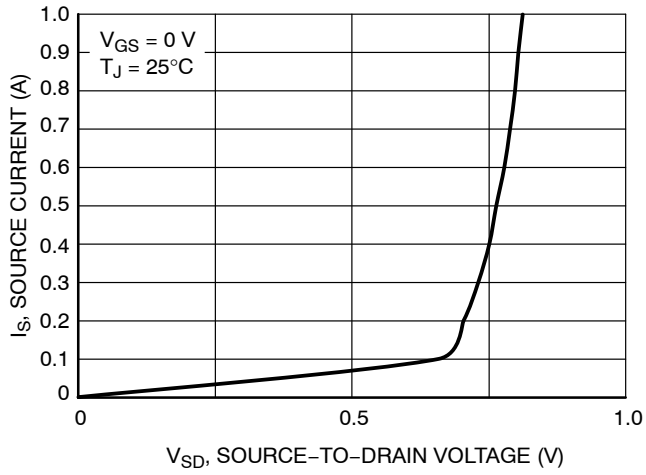


Figure 10. Diode Forward Voltage vs. Current

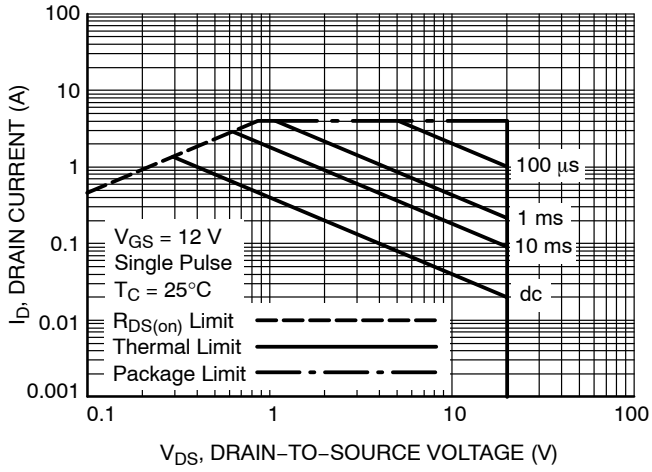
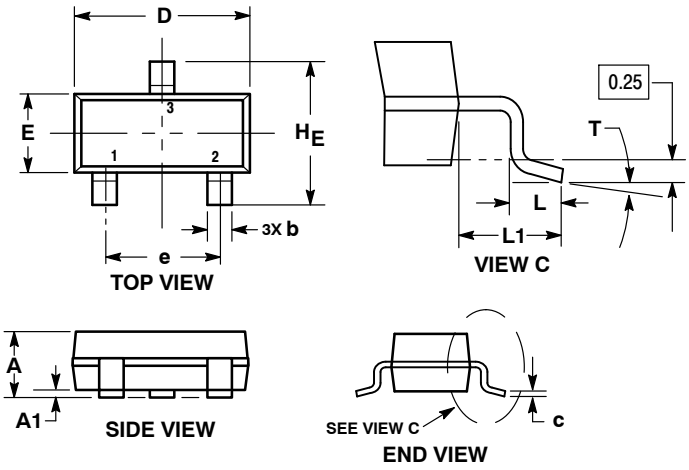


Figure 11. Maximum Rated Forward Biased Safe Operating Area

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−08
ISSUE AR

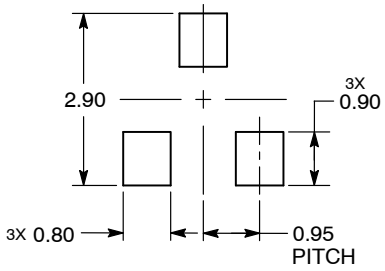


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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